NSN 5961-01-049-8367

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Photo Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-049-8367 **Inclosure Material:** Plastic **Overall Length:** Between 0.170 inches and 0.210 inches **Overall Height:** Between 0.125 inches and 0.165 inches **Overall Width:** 0.205 inches **Internal Configuration:** Junction contact **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 50.0 collector to base voltage/static/emitter open and 50.0 collector to emitter voltage/static/base open and 5.0 emitter to base voltage, static, collector open **Current Rating Per Characteristic:** 0.10 microamperes source cutoff current pascal and 700.00 microamperes forward current, total rms minor **Special Features:** Junction pattern arrangement: npn **Terminal Type And Quantity:** 3 uninsulated wire lead Shelf Life: N/a **Unit Of Measure:** Demilitarization: Yes - demil/mli Fiig: